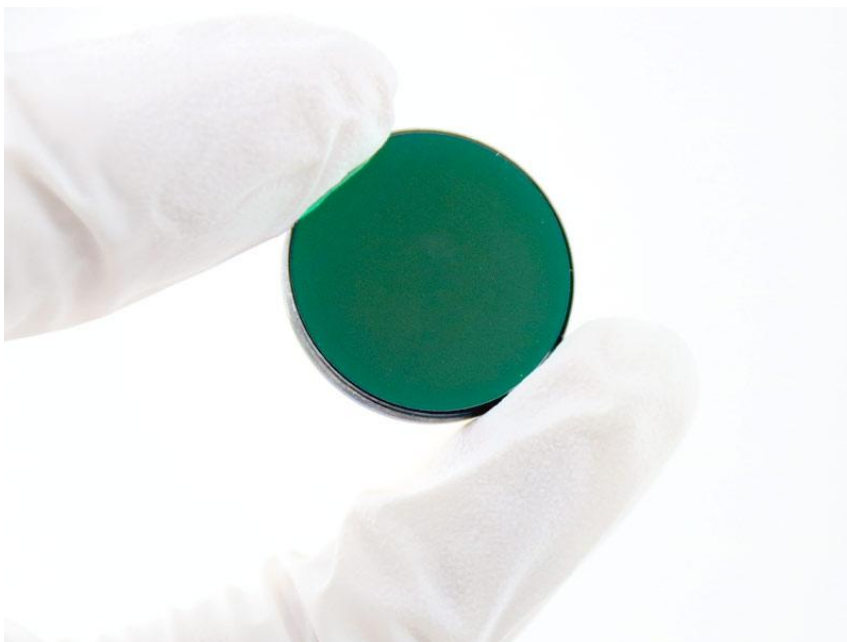




4720nm 红外滤光片



描述

高透过率，减少光学系统的信号损失，提升光学系统的性能，适用于激光系统、光谱分析、气体分析和其他高端光学应用。

产品特点

特定波长选择性、高透过率、耐用材料

产品型号

NB-4720-090 nm

应用领域

气体分析

研究与测试



核心参数

中心波长	半宽高带宽	透射率	气体	基材
4720nm	90nm	70%	CO	Sapphire

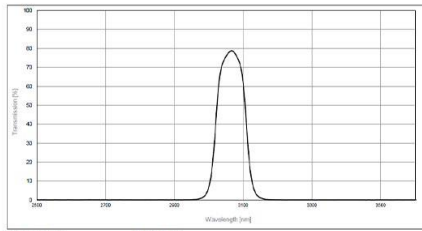
详细参数

型号	中心 波长 (nm)	中心 波长 偏差 (nm)	半宽 高带 宽 (nm)	半宽 高带 宽偏 差 (nm)	透射 率 %	气体	基材	Blocki ng(nm)
BP-3050-10 0 nm	3050	± 30	100	± 20	70	C ₂ H ₂	Sapph ire	30 000
NB-3275-0 80 nm	3275	± 20	80	± 20	70	HC	Sapph ire	30 000
NB-3355-0 40 nm	3355	± 20	40	± 10	70	C ₂ H ₆	Sapph ire	30 000
BP-3400-12 0 nm	3400	± 30	120	± 20	70	HC	Sapph ire	30 000
BP-3400-12 0 nm Si	3400	± 30	120	± 20	70	HC	Silicon	11 000

NB-3910-0 70 nm	3910	± 30	70	± 15	70	Ref	Silicon	11 000
BP-4265-20 0 nm	4265	± 30	180	± 20	70	CO ₂	Sapph ire	30 000
NB-4265-1 20 nm Si	4265	± 30	120	± 20	70	CO ₂	Silicon	11 000
NB-4525-0 83 nm	4525	± 20	83	± 6	70	N ₂ O	Sapph ire	30 000
NB-4525-0 83 nm Si	4525	± 20	83	± 6	70	N ₂ O	Silicon	11 000
BP-4650-18 0 nm	4650	± 40	180	± 20	70	CO	Sapph ire	30 000
BP-4650-18 0 nm Si	4650	± 40	180	± 20	70	CO	Silicon	11 000
NB-4720-0 90 nm	4720	± 20	90	± 10	70	CO	Sapph ire	30 000
NB-4720-0 90 nm Si	4720	± 20	90	± 10	70	CO	Silicon	11 000
NB-5680-1 65 nm	5680	± 40	165	± 30	60	H ₂ O	Sapph ire	30 000

NB-5680-1 65 nm Si	5680	± 40	165	± 30	70	H ₂ O	Silicon	11 000
NB-6250-1 00 nm	6250	± 40	100	± 30	70	NO ₂	Silicon	11 000
BP-6580-20 0 nm	6580	± 40	200	± 20	70	H ₂ O	Silicon	14 000
NB-7300-1 80 nm	7300	± 50	180	± 20	70	SO ₂	Silicon	11 000
BP-7675-24 2 nm	7675	± 50	242	± 30	70	CH ₄	Silicon	12 000
BP-10540-6 90 nm	10540	± 100	690	± 100	70	SF ₆	Ge	16 500
BP-10540-6 90 nm Si	10540	± 100	690	± 100	60	SF ₆	Silicon	16 500

特性曲线

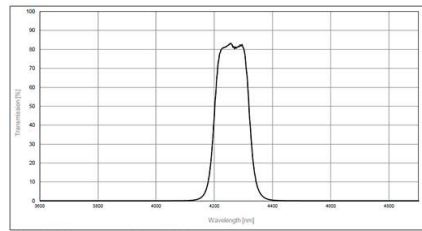


Measured values:
 CWL = 304.82 nm...OK
 FWH = 80.88 nm...OK
 Cuton 5 % = 297.03 nm
 Cutoff 5 % = 313.53 nm
 HP1 = 3013.88 nm
 HP2 = 3130.26 nm
 Tpeak = 78.75 %
 Tavg = 75.66 %
 Slope 1 = 1.11 %
 Slope 2 = 1.09 %

Transmittance:
 T high min 3037 ~ 3092 nm = 78.75 %...OK

Date:
 Operator:
Article:
 Art no: 713M
 NB-3055-500 nm
Specifications:
 CWL: 3050 ±30 nm
 FWH: 100 ±20 nm
 B: 100 ~ 3000 nm avg 0.1%
 T high min 70 %

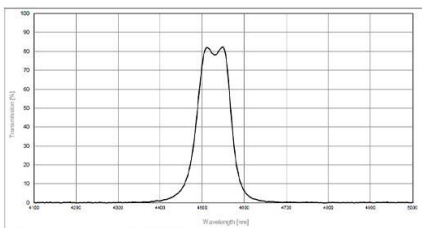
Measurement conditions:
 Temperature: 296 K ADR: 0 °



Measured values:
 CWL = 4260.43 nm...OK
 FWH = 123.92 nm...OK
 Cuton 5 % = 4169.36 nm
 Cutoff 5 % = 4354.69 nm
 HP1 = 4198.47 nm
 HP2 = 4322.39 nm
 Tpeak = 83.29 %
 Tavg (HP1 HP2) = 75.16 %...OK
 Slope 1 = 0.96 %
 Slope 2 = 0.98 %

Date:
 Operator:
Article:
 Art no: 7113M
 BP-4265-120 nm Si
Specifications:
 CWL: 4265 ±30 nm
 FWH: 120 ±20 nm
 Tavg: 70 %
 B: 100 ~ 10000 nm avg 0.1%
 T avg min 70 %

Measurement conditions:
 Temperature: 296 K ADR: 0 °

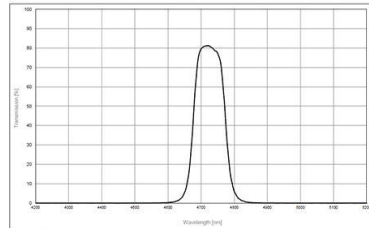


Measured values:
 CWL = 4528.1 nm...OK
 FWH = 80.83 nm...OK
 Cuton 5 % = 4542.62 nm
 Cutoff 5 % = 4603.96 nm
 HP1 = 4605.18 nm
 HP2 = 4573.61 nm
 Tpeak = 82.37 %
 Tavg = 80.07 %
 Slope 1 = 1.19 %
 Slope 2 = 0.92 %

Transmittance:
 T avg min 4503 ~ 4555 nm = 80.19 %...OK

Date:
 Operator:
Article:
 Art no: 713M
 NB-4525-083 nm Si
Specifications:
 CWL: 4525 ±20 nm
 FWH: 83 ±5 nm
 B: 100 ~ 10000 nm avg 0.1%
 T avg min 70 %

Measurement conditions:
 Temperature: 296 K ADR: 0 °



Measured values:
 CWL = 4725.15 nm...OK
 FWH = 89.2 nm...OK
 Cuton 5 % = 4648.73 nm
 Cutoff 5 % = 4803.27 nm
 HP1 = 4675.55 nm
 HP2 = 4774.25 nm
 Tpeak = 81.25 %...OK
 Tavg = 79.6 %
 Slope 1 = 0.78 %
 Slope 2 = 0.69 %

Date:
 Operator:
Article:
 Art no: 7113M
 NB-4725-115 nm
Specifications:
 CWL: 4720 ±20 nm
 FWH: 90 ±10 nm
 Tavg: 79 %
 Blocking: 200 ~ 30000 nm (OD 3)

Measurement conditions:
 Temperature: 23 °C
 ADR: 0 deg